

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CBR8M-L010M SERIES

GLASS PASSIVATED JUNCTION
SILICON BRIDGE RECTIFIER
8.0 AMP, 100 THRU 1000 VOLTS

CASE DMM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR8M-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

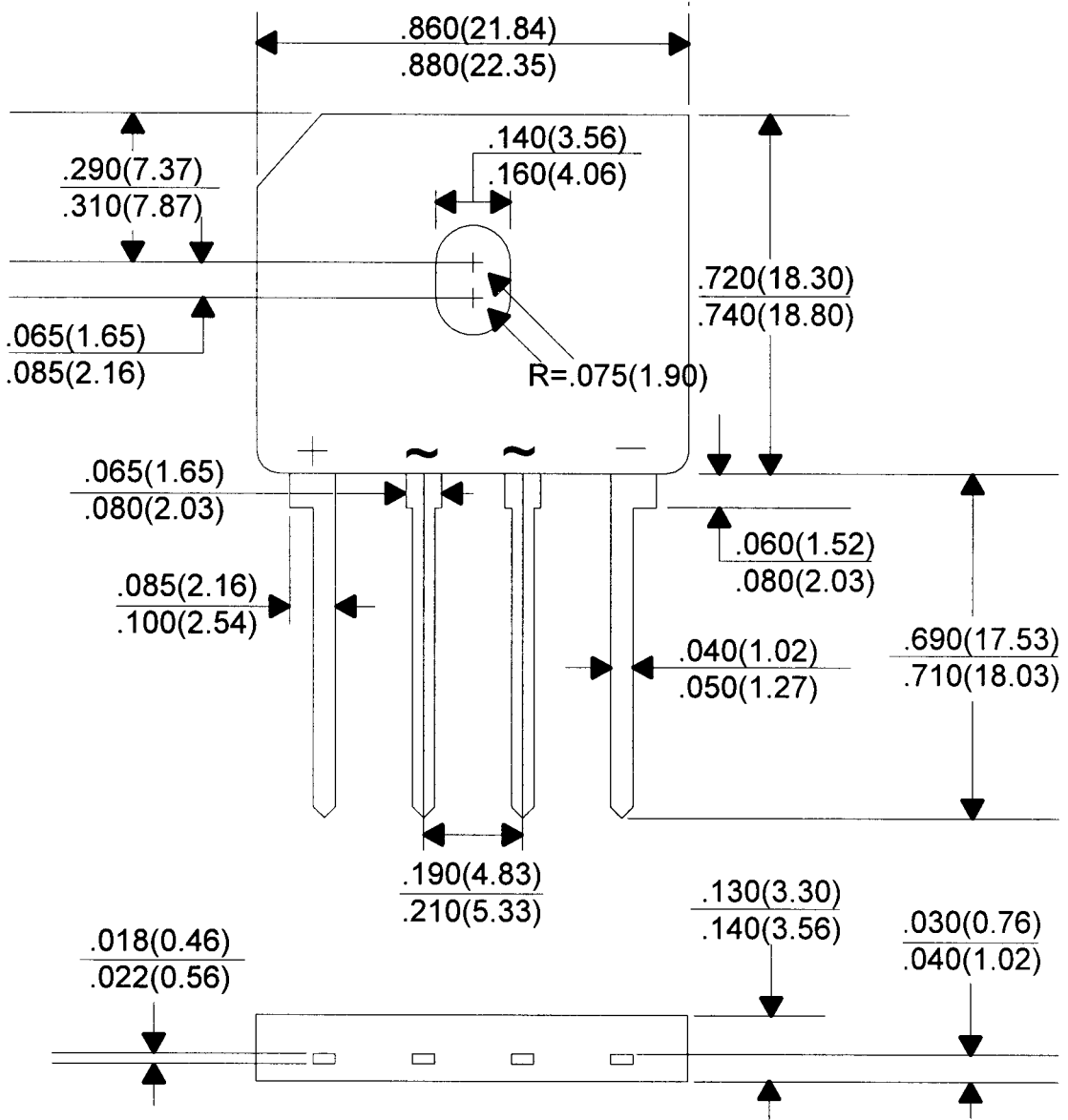
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| | SYMBOL | CBR8M -L010M | CBR8M -L020M | CBR8M -L040M | CBR8M -L060M | CBR8M -L080M | CBR8M -L100M | UNITS |
|---|----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|--------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| DC Blocking Voltage | V_R | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| RMS Reverse Voltage | $V_{R(RMS)}$ | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Average Forward Current ($T_C=100^\circ\text{C}$) | I_O | | | | 8.0 | | | A |
| Peak Forward Surge Current | I_{FSM} | | | | 200 | | | A |
| Operating and Storage Junction Temperature | T_J, T_{stg} | | | | -65 to +150 | | | $^\circ\text{C}$ |
| Thermal Resistance | θ_{JC} | | | | 3.0 | | | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--------|--|-----|-----|-----|---------------|
| I_R | V_R =Rated V_{RRM} | | | 5.0 | μA |
| I_R | V_R =Rated V_{RRM} , $T_C=100^\circ\text{C}$ | | | 500 | μA |
| V_F | $I_F=8.0\text{A}$ | | | 1.0 | V |
| C_J | $V_R=4.0\text{V}$, $f=1.0\text{MHz}$ | | 260 | | pF |

CASE DMM - MECHANICAL OUTLINE



All Dimensions in Inches (mm).